

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior versions of claims in the application.

1. (Currently amended): A method of forming a micro pattern comprising steps of:

(a) coating photosensitive resist material over a substrate and exposing and developing the photosensitive resist material to form a resist pattern; and

(b) etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and an SO<sub>2</sub> gas, the first gas comprising at least one gas selected from the group consisting of He, Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>,

wherein in the step (b), a flow rate of the first gas is equal to or larger than 40 % of a flow rate of the mixture gas.

2. (Original): A method of forming a micro pattern according to claim 1, wherein the mixture gas additionally comprises an O<sub>2</sub> gas.

3. (Cancelled).

4. (Original): A method of forming a micro pattern according to claim 1, wherein in the step (b), the etching is performed in a state that a temperature of the substrate is maintained at 40 °C or lower.

5. (Original): A method of forming a micro pattern according to claim 1, wherein:

the substrate has an antireflection film made of organic substance and formed over an underlying surface; and

in the step (b), the surface layer of the resist pattern is etched, and by using the resist pattern as a mask, the antireflection film is etched.

6. (Original): A method of forming a micro pattern according to claim 5, wherein the mixture gas comprises an O<sub>2</sub> gas.

7. (Original): A method of forming a micro pattern according to claim 6, wherein the step (b) includes a step of increasing a ratio of a flow rate of the SO<sub>2</sub> gas to a flow rate of the O<sub>2</sub> gas during the etching.

8. (Original): A method of forming a micro pattern according to claim 7, wherein in the step (b), the flow rate ratio of the SO<sub>2</sub> gas is increased when the time necessary for etching a whole thickness of the antireflection film lapses.

9. (Original): A method of forming a micro pattern according to claim 2, wherein:

the substrate has an antireflection film made of organic substance and formed over an underlying surface; and

in the step (b), the surface layer of the resist pattern is etched, and by using the resist pattern as a mask, the antireflection film is etched.

10. (Currently amended): A method of manufacturing a semiconductor device comprising steps of:

- (i) forming a first film over a semiconductor substrate;
- (j) forming an antireflection film made of organic substance over the first film;
- (k) forming a resist film made of photosensitive resist material over the antireflection film;
- (l) exposing and developing the resist film to form a resist pattern;
- (m) etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and an SO<sub>2</sub> gas, the first gas comprising at least one gas selected from the group consisting of He, Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>, and by using the resist pattern as a mask, patterning the antireflection film;
- (n) etching the first film by using as a mask the resist pattern whose surface layer was etched and the patterned antireflection film; and
- (o) removing the resist pattern and the antireflection film;

wherein in the step (m), a flow rate of the first gas is equal to or larger than 40 %  
of a flow rate of the mixture gas.

11. (Original): A method of manufacturing a semiconductor device according to claim 10,  
wherein:

the step (i) comprises a step of forming a second film over the semiconductor  
substrate and forming the first film over the second film; and

the method further comprises a step of etching the second film by using the first  
film as a hard mask, after the step (n).

12. (Original): A method of manufacturing a semiconductor device according to claim 10,  
wherein the mixture gas additionally comprises an O<sub>2</sub> gas.

13. (Cancelled).

14. (Original): A method of manufacturing a semiconductor device according to claim 10,  
wherein in the step (m), the etching is performed in a state that a temperature of the substrate is  
maintained at 40 °C or lower.

15. (Original): A method of manufacturing a semiconductor device according to claim 10, wherein the mixture gas comprises an O<sub>2</sub> gas and the step (m) comprises a step of increasing a ratio of a flow rate of the SO<sub>2</sub> gas to a flow rate of the O<sub>2</sub> gas during the etching.

16. (Original): A method of manufacturing a semiconductor device according to claim 15, wherein in the step (m), the flow rate ratio of the SO<sub>2</sub> gas is increased when the time necessary for etching a whole thickness of the antireflection film lapses.

17. (Currently amended): A method of forming a micro pattern comprising steps of:

coating photosensitive resist material over a substrate and exposing and developing the photosensitive resist material to form a resist pattern; and

etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and a second gas, the first gas comprising at least one gas selected from the group consisting of He, Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>, and the second gas forming polymer that comprises sulfur; wherein the mixture gas further comprises an O<sub>2</sub> gas.

18. (Cancelled).

19. (Currently amended): A method of manufacturing a semiconductor device comprising steps of:

forming a first film over a semiconductor substrate;  
forming an antireflection film made of organic substance over the first film;  
forming a resist film made of photosensitive resist material over the antireflection film;  
exposing and developing the resist film to form a resist pattern;  
etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and a second gas, and patterning the antireflection film by using the resist pattern as a mask, the first gas comprising at least one gas selected from the group consisting of He, Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>, and the second gas forming polymer that comprises sulfur;  
etching the first film by using as a mask the resist pattern whose surface layer was etched and the patterned antireflection film; and  
removing the resist pattern and the antireflection film; wherein the mixture gas further comprises an O<sub>2</sub> gas.

20. (Cancelled).

21. (Original): A method of forming a micro pattern according to claim 11, wherein a gate electrode is formed by etching the second film, and further comprising a step of implanting ions to form source and drain regions after the step (o).

22. (Original): A method of forming a micro pattern according to claim 1, wherein said photosensitive resist material and said antireflection film are over-etched to reduce the size of the photosensitive resist material and the antireflection film.

23. (Previously presented): A method of forming a micro pattern according to claim 1, wherein the etching of the resist pattern reduces the width of the resist pattern.

24. (Previously presented): A method of manufacturing a semiconductor device according to claim 10, wherein the etching of the resist pattern reduces the width of the resist pattern.

25. (Previously presented): A method of forming a micro pattern according to claim 17, wherein the etching of the resist pattern reduces the width of the resist pattern.

26. (Previously presented): A method of manufacturing a semiconductor device according to claim 19, wherein the etching of the resist pattern reduces the width of the resist pattern.

27. (New): A method of forming a micro pattern comprising steps of:

(a) coating photosensitive resist material over a substrate and exposing and developing the photosensitive resist material to form a resist pattern; and

(b) etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and an SO<sub>2</sub> gas, the first gas comprising at least one gas selected from the group consisting of Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>.

28. (New): A method of manufacturing a semiconductor device comprising steps of:

- (i) forming a first film over a semiconductor substrate;
- (j) forming an antireflection film made of organic substance over the first film;
- (k) forming a resist film made of photosensitive resist material over the antireflection film;
- (l) exposing and developing the resist film to form a resist pattern;
- (m) etching a surface layer of sidewalls and a top wall of the resist pattern by plasma of a mixture gas comprising a first gas and an SO<sub>2</sub> gas, the first gas comprising at least one gas selected from the group consisting of Ne, Ar, Xe, Kr, CO, CO<sub>2</sub> and N<sub>2</sub>, and by using the resist pattern as a mask, patterning the antireflection film;
- (n) etching the first film by using as a mask the resist pattern whose surface layer was etched and the patterned antireflection film; and
- (o) removing the resist pattern and the antireflection film.